



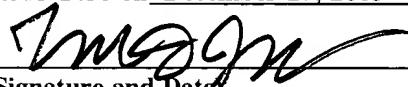
IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Yasuo TARUI, et al.  
Serial No. : 09/801,990  
Filed : March 8, 2001  
For : TRANSISTOR-TYPE FERROELECTRICNONVOLATILE  
MEMORY ELEMENT  
Group Art Unit : 2818

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(Signature and Date)

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INFORMATION DISCLOSURE STATEMENT

Sir:

Attached hereto is a copy of a European Search Report dated October 6, 2003 along with Form PTO-1449 and copies of the five cited references listed therein.

This Information Disclosure Statement is being filed prior to issuance of the first Official Action. Therefore, there is no charge for filing this IDS.

Respectfully submitted,

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F-6888

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INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)				Applicant: Yasuo TARUI, et al.			
				Filing Date: March 8, 2001		Group: 2818	
<b>U.S. PATENT DOCUMENTS</b>							
Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
		5,978,253	11/2/99	Lee et al.			
		6,025,627	2/15/00	Forbes et al.			
		5,990,515	11/23/99	Liu et al.			
<b>FOREIGN PATENT DOCUMENTS</b>							
		Document Number	Date	Country	Class	Subclass	Translation
		0 940 856	9/8/99	EP			Yes      No
N <sup>F</sup>							
TRANSLATION KEY: * English Abstract. <sup>F</sup> Concise statement of relevance provided in foreign search report. <sup>C</sup> Concise statement of relevance provided in specification. <sup>S</sup> Concise statement of relevance provided in IDS. <sup>P</sup> Relevant portion of reference translated. <sup>O</sup> English abstract only - copy of reference in pct search.							
<b>OTHER INFORMATION DISCLOSURE CITATIONS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>							
		"Electrical Properties of MFIS-and MFMIS-FETs Using Ferroelectric SrBi <sub>2</sub> Ta <sub>2</sub> O <sub>9</sub> Film and SrTa <sub>2</sub> O <sub>6</sub> /SiON Buffer Layer" Extended Abstracts of the International Conference on Solid State Devices and Materials, Japan Society of Applied Physics, Tokyo, Japan; 1999, pages 404-405, XP000935143; *page 405; figure 1*					
EXAMINER				DATE CONSIDERED			
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							